

# 74AUP1G79

Low-power D-type flip-flop; positive-edge trigger

Rev. 03 — 3 August 2009

Product data sheet

## 1. General description

---

The 74AUP1G79 provides the single positive-edge triggered D-type flip-flop. Information on the data input is transferred to the Q output on the LOW-to-HIGH transition of the clock pulse. The D input must be stable one setup time prior to the LOW-to-HIGH clock transition for predictable operation.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

## 2. Features

---

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM JESD22-A114E Class 3A exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101-C exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu\text{A}$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of  $V_{CC}$
- $I_{OFF}$  circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

### 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G79GV	-40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74AUP1G79GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G79GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1G79GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

### 4. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP1G79GV	p79
74AUP1G79GW	pP
74AUP1G79GM	pP
74AUP1G79GF	pP

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5. Functional diagram

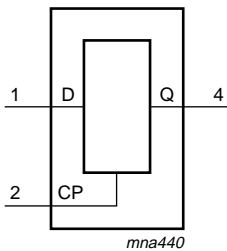


Fig 1. Logic symbol

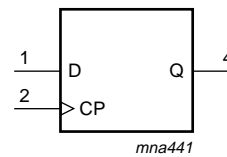


Fig 2. IEC logic symbol

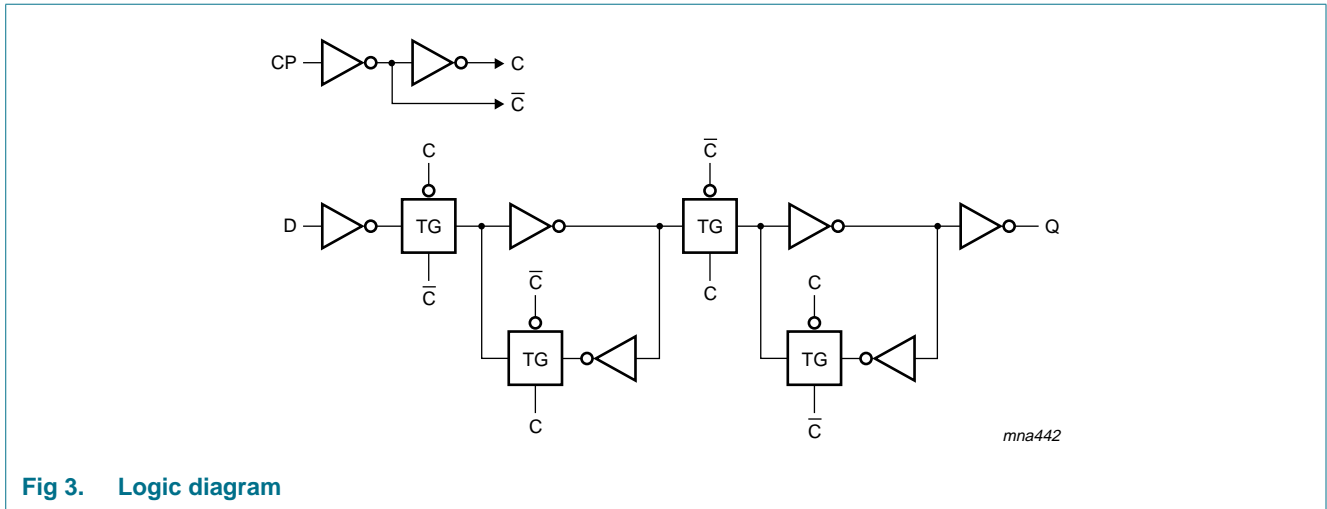


Fig 3. Logic diagram

## 6. Pinning information

### 6.1 Pinning

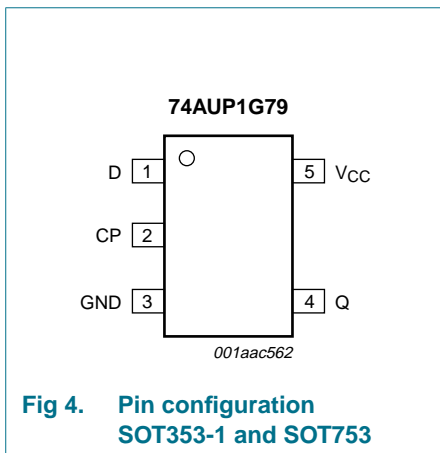


Fig 4. Pin configuration SOT353-1 and SOT753

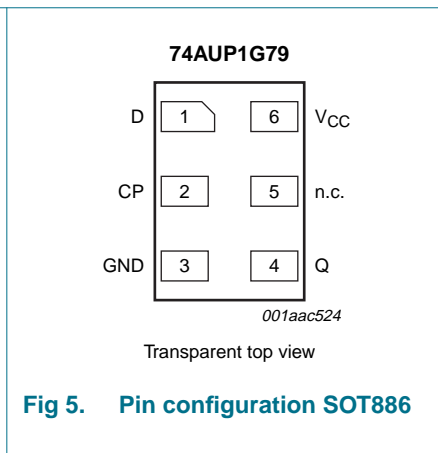


Fig 5. Pin configuration SOT886

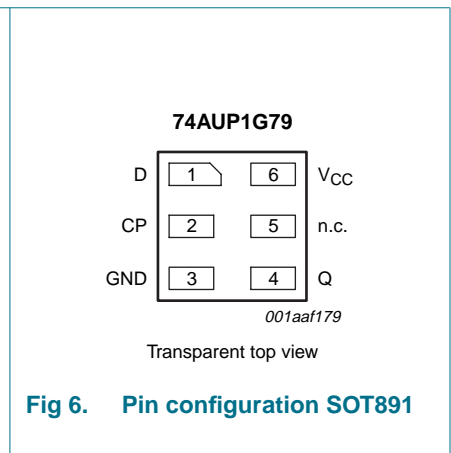


Fig 6. Pin configuration SOT891

### 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1/SOT753	SOT886/SOT891	
D	1	1	data input D
CP	2	2	clock pulse input CP
GND	3	3	ground (0 V)
Q	4	4	data output Q
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

## 7. Functional description

**Table 4.** Function table<sup>[1]</sup>

Input		Output
CP	D	Q
↑	L	L
↑	H	H
L	X	q

- [1] H = HIGH voltage level;  
 L = LOW voltage level;  
 ↑ = LOW-to-HIGH CP transition;  
 X = don't care;  
 q = lower case letter indicates the state of referenced input, one setup time prior to the LOW-to-HIGH CP transition.

## 8. Limiting values

**Table 5.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-50	-	mA
$V_I$	input voltage		[1] -0.5	+4.6	V
$I_{OK}$	output clamping current	$V_O < 0$ V	-50	-	mA
$V_O$	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	±20	mA
$I_{CC}$	supply current		-	50	mA
$I_{GND}$	ground current		-50	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.  
 [2] For TSSOP5 and SC-74A packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.  
 For XSON6 packages: above 118 °C the value of  $P_{tot}$  derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

**Table 6.** Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0.8	3.6	V
$V_I$	input voltage		0	3.6	V
$V_O$	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.75 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.11	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.32	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.2	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.2	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI <sub>CC</sub>	additional supply current	per pin; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<a href="#">[1]</a>	-	40	μA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 0 V to 3.6 V; V <sub>I</sub> = GND or V <sub>CC</sub>	-	0.8	-	pF
C <sub>O</sub>	output capacitance	V <sub>O</sub> = GND; V <sub>CC</sub> = 0 V	-	1.7	-	pF

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.7 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.03	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.30	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.97	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.85	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.67	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.5	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.6	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI <sub>CC</sub>	additional supply current	per pin; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	[1] -	-	50	μA

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.75 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.25 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.6 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	0.93	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.17	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.77	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.67	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.40	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.33 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.75	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.75	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI <sub>CC</sub>	additional supply current	per pin; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	[1]	-	75	μA

[1] One input at V<sub>CC</sub> - 0.6 V, other input at V<sub>CC</sub> or GND.

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min (85 °C)	Max (85 °C)	Min (125 °C)	Max (125 °C)	
<b>C<sub>L</sub> = 5 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q; see <a href="#">Figure 7</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	19.7	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.6	5.5	11.0	2.4	12.9	2.4	14.2	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.0	3.8	7.0	1.8	8.1	1.8	9.0	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.7	3.1	5.4	1.5	6.4	1.5	7.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.4	2.3	4.0	1.1	4.7	1.1	5.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.2	2.0	3.4	0.9	4.0	0.9	4.4	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	53	-	-	-	-	-	MHz
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	203	-	170	-	170	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	347	-	310	-	300	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	435	-	400	-	390	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	550	-	490	-	480	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	619	-	550	-	510	-	MHz
<b>C<sub>L</sub> = 10 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q; see <a href="#">Figure 7</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	23.1	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.1	6.3	12.3	2.8	14.4	2.8	15.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.5	4.4	8.1	2.2	9.5	2.2	10.5	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.1	3.6	6.3	1.9	7.5	1.9	8.3	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.8	2.8	4.7	1.5	5.6	1.5	6.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.7	2.5	4.1	1.3	4.5	1.3	5.0	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	52	-	-	-	-	-	MHz
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	192	-	150	-	150	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	324	-	280	-	230	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	421	-	310	-	250	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	486	-	370	-	360	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	550	-	410	-	360	-	MHz



**Table 8. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min (85 °C)	Max (85 °C)	Min (125 °C)	Max (125 °C)	
<b>C<sub>L</sub> = 15 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q; see <a href="#">Figure 7</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	26.6	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.5	7.1	13.6	3.2	15.6	3.2	17.2	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.8	5.0	9.2	2.5	10.7	2.5	11.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.4	4.1	7.1	2.2	8.5	2.2	9.4	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.2	3.2	5.4	1.9	6.3	1.9	7.0	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	2.9	4.5	1.6	5.0	1.6	5.5	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	50	-	-	-	-	-	MHz
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	181	-	120	-	120	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	301	-	190	-	160	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	407	-	240	-	190	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	422	-	300	-	270	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	481	-	320	-	300	-	MHz
<b>C<sub>L</sub> = 30 pF</b>										
t <sub>pd</sub>	propagation delay	CP to Q; see <a href="#">Figure 7</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 0.8 V	-	36.8	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.7	9.3	17.3	4.2	23.3	4.2	25.6	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.8	6.4	11.8	3.3	14.3	3.3	15.7	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.3	5.3	9.4	3.0	11.3	3.0	12.4	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.0	4.3	7.0	2.7	8.5	2.7	9.4	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.8	3.9	5.8	2.6	7.2	2.6	7.9	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	28	-	-	-	-	-	MHz
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	128	-	70	-	70	-	MHz
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	206	-	120	-	110	-	MHz
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	262	-	150	-	120	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	269	-	190	-	170	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	309	-	200	-	190	-	MHz

**Table 8. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

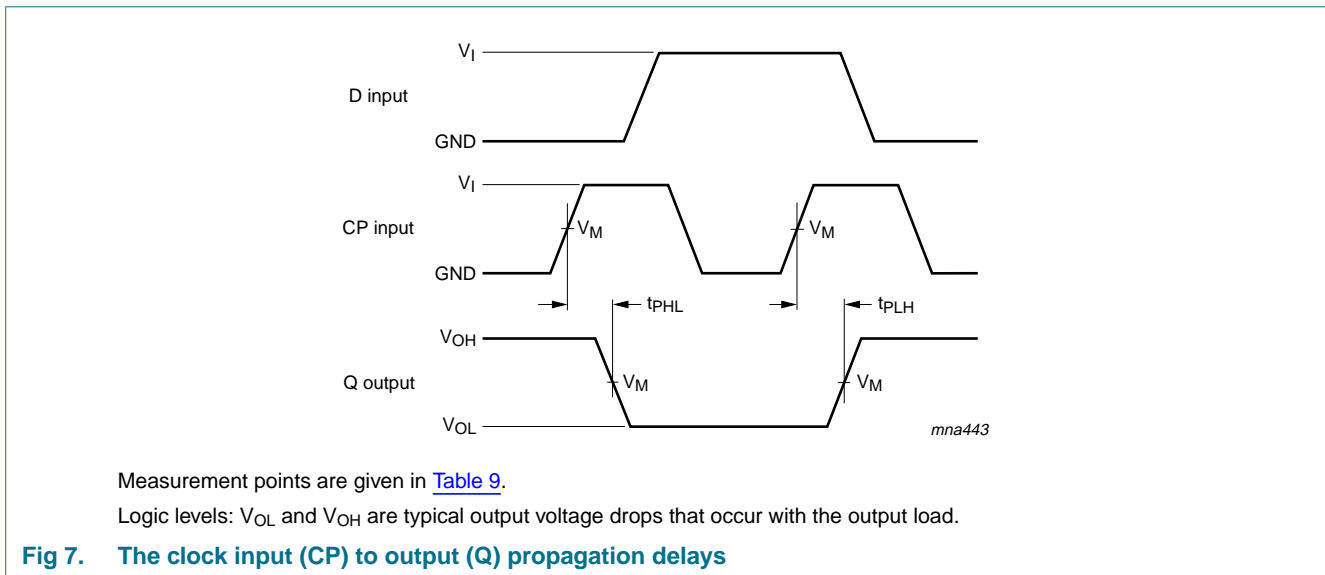
Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min (85 °C)	Max (85 °C)	Min (125 °C)	Max (125 °C)	
<b>C<sub>L</sub> = 5 pF, 10 pF, 15 pF and 30 pF</b>										
t <sub>su</sub>	set-up time	HIGH; D to CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	3.4	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	0.8	-	1.6	-	1.4	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	0.5	-	1.0	-	1.0	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.5	-	0.9	-	0.9	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.4	-	0.7	-	0.7	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	0.4	-	0.6	-	0.6	-	ns
		LOW; D to CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	3.0	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	0.9	-	1.4	-	1.4	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	0.6	-	1.0	-	1.0	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.5	-	0.9	-	0.9	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.5	-	0.8	-	0.8	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	0.7	-	1.0	-	1.0	-	ns
t <sub>h</sub>	hold time	D to CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	-1.9	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	-0.6	-	0.2	-	0.2	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	-0.4	-	0	-	0	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	-0.4	-	0	-	0	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-0.4	-	0	-	0	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-0.3	-	0	-	0	-	ns
t <sub>w</sub>	pulse width	HIGH or LOW; CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 0.8 V	-	5.6	-	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.4	-	3.5	-	3.5	-	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	1.3	-	2.0	-	2.0	-	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.9	-	1.9	-	1.9	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.7	-	2.0	-	2.0	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	0.6	-	2.2	-	2.2	-	ns

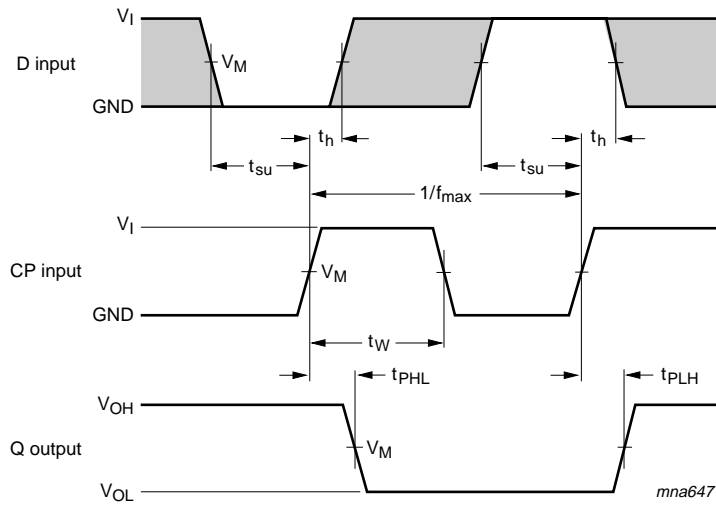
**Table 8. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C				Unit
			Min	Typ <sup>[1]</sup>	Max	Min (85 °C)	Max (85 °C)	Min (125 °C)	Max (125 °C)	
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <sup>[3]</sup>								
		V <sub>CC</sub> = 0.8 V	-	1.6	-	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	1.7	-	-	-	-	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	1.8	-	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	1.9	-	-	-	-	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	2.3	-	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	2.7	-	-	-	-	pF	

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.
- [3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

## 12. Waveforms





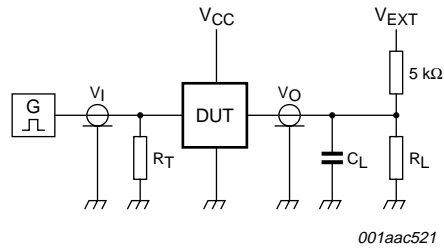
Measurement points are given in [Table 9](#).

Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage drops that occur with the output load.

**Fig 8.** The clock input (CP) to output (Q) propagation delays, CP clock pulse width, D to CP setup times, CP to D hold times and the CP maximum frequency

**Table 9.** Measurement points

Supply voltage	Output	Input		
$V_{CC}$	$V_M$	$V_M$	$V_I$	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{CC}$	$\leq 3.0$ ns



Test data is given in [Table 10](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 9. Load circuitry for switching times**

**Table 10. Test data**

Supply voltage	Load		$V_{EXT}$		
$V_{CC}$	$C_L$	$R_L$ [1]	$t_{PLH}, t_{PHL}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Fig 10. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

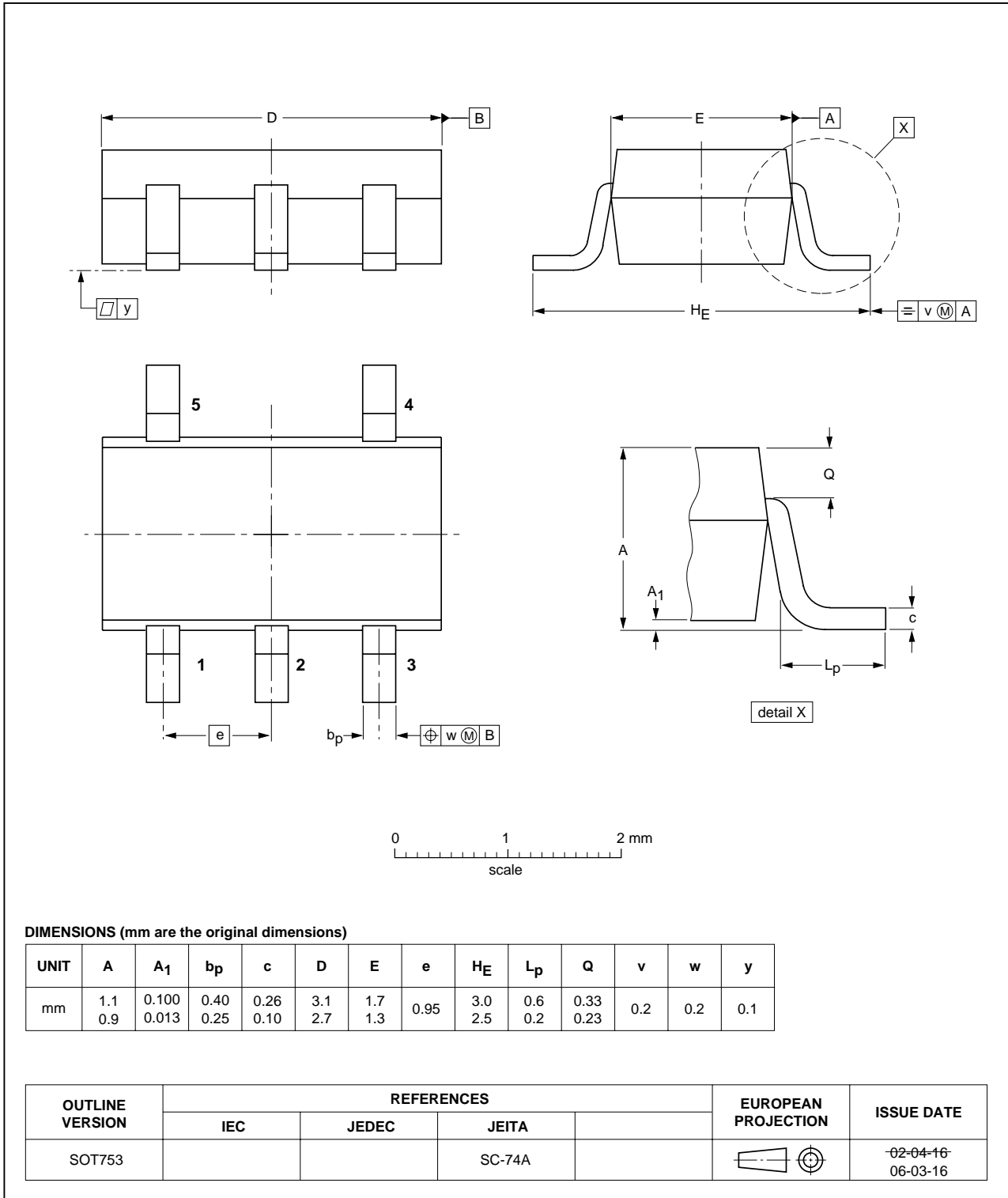


Fig 11. Package outline SOT753 (SC-74A)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

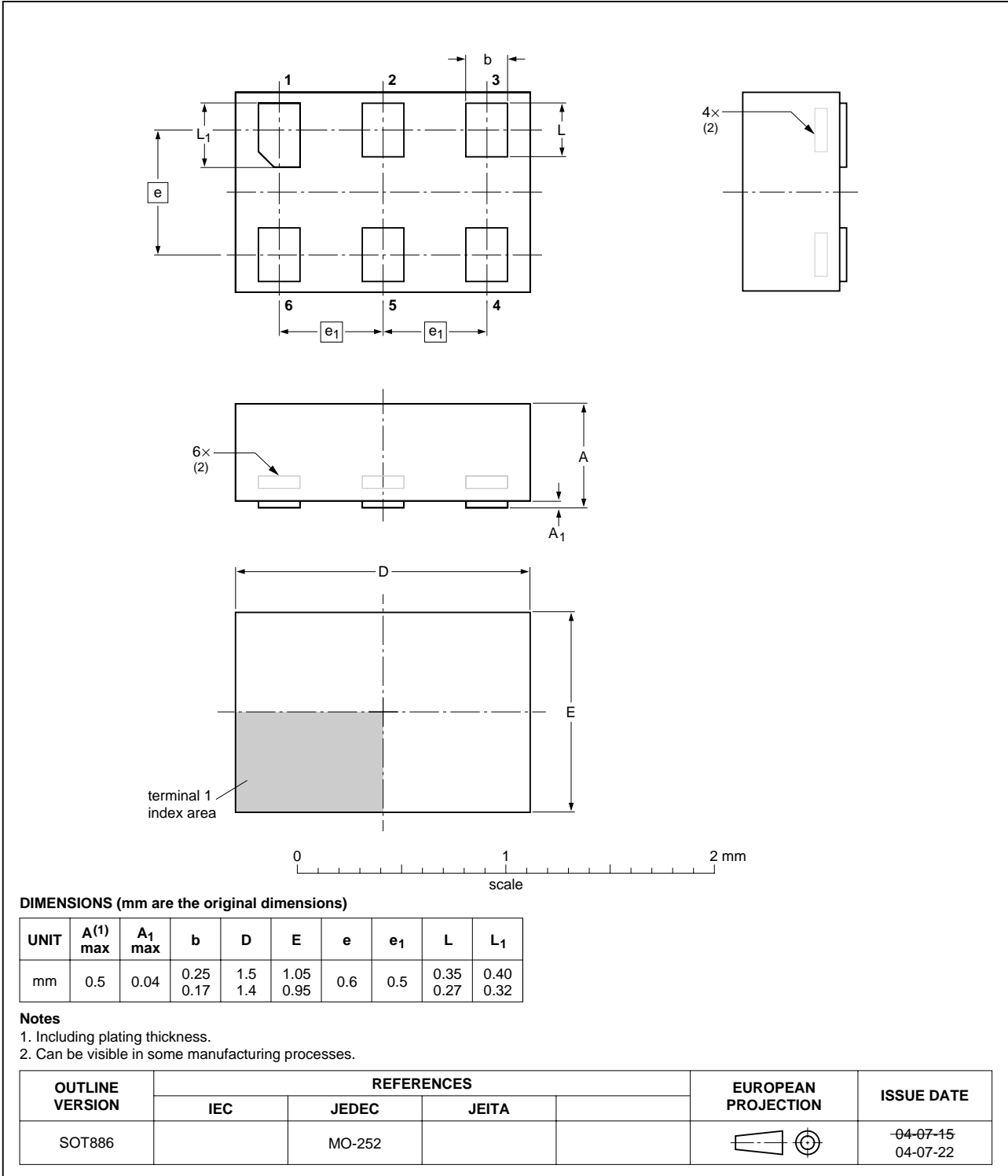


Fig 12. Package outline SOT886 (XSON6)



XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

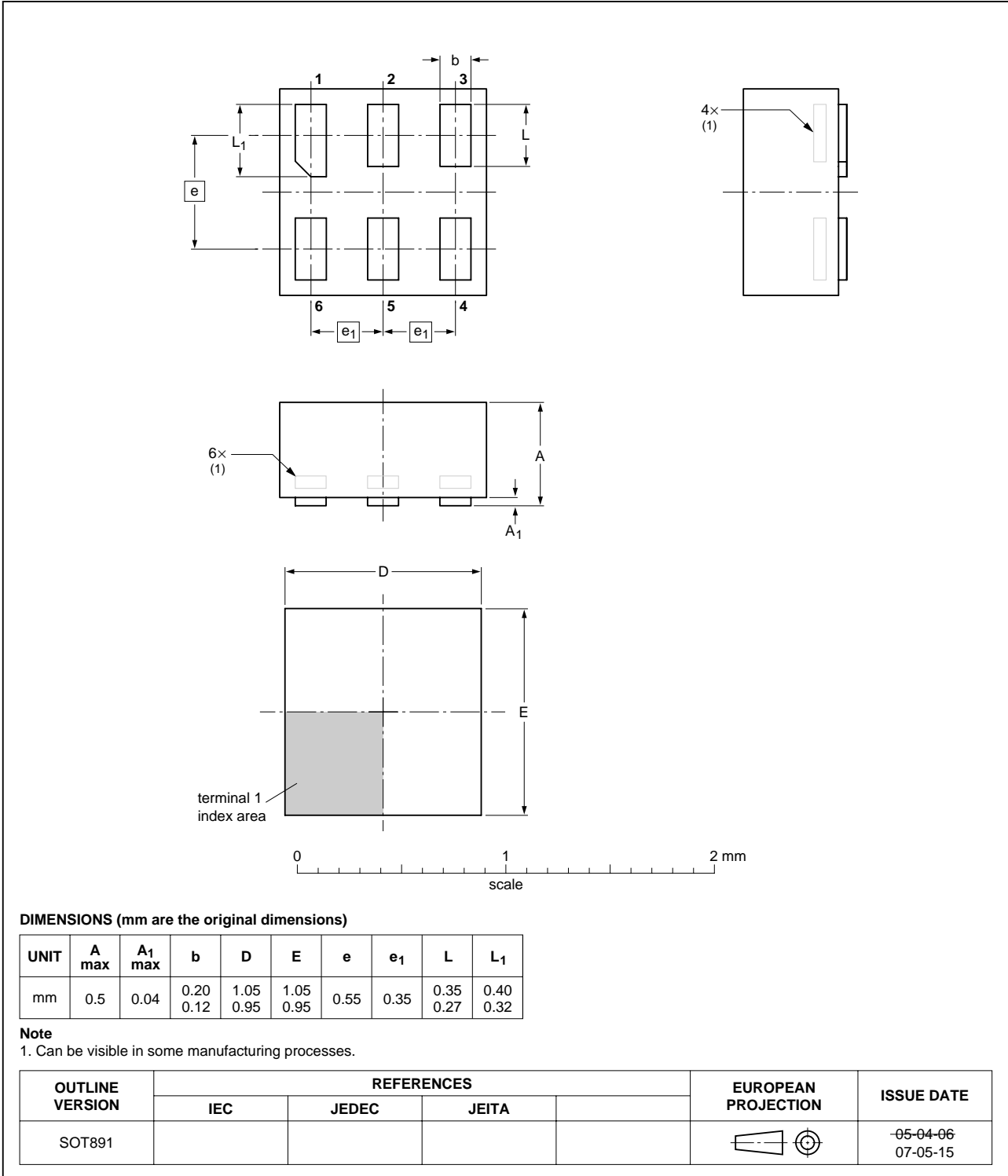


Fig 13. Package outline SOT891 (XSON6)

## 14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G79_3	20090803	Product data sheet	-	74AUP1G79_2
Modifications:	• Added type number 74AUP1G79GV (SC-74A) package.			
74AUP1G79_2	20061017	Product data sheet	-	74AUP1G79_1
74AUP1G79_1	20050912	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 16.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

### 16.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Terms and conditions of sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

### 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 17. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

**18. Contents**

1 **General description** . . . . . 1

2 **Features** . . . . . 1

3 **Ordering information** . . . . . 2

4 **Marking** . . . . . 2

5 **Functional diagram** . . . . . 2

6 **Pinning information** . . . . . 3

6.1 Pinning . . . . . 3

6.2 Pin description . . . . . 3

7 **Functional description** . . . . . 4

8 **Limiting values** . . . . . 4

9 **Recommended operating conditions** . . . . . 4

10 **Static characteristics** . . . . . 5

11 **Dynamic characteristics** . . . . . 8

12 **Waveforms** . . . . . 11

13 **Package outline** . . . . . 14

14 **Abbreviations** . . . . . 18

15 **Revision history** . . . . . 18

16 **Legal information** . . . . . 19

16.1 Data sheet status . . . . . 19

16.2 Definitions . . . . . 19

16.3 Disclaimers . . . . . 19

16.4 Trademarks . . . . . 19

17 **Contact information** . . . . . 19

18 **Contents** . . . . . 20

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2009.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

Date of release: 3 August 2009

Document identifier: 74AUP1G79\_3



## Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331